

L Number	Hits	Search Text	DB	Time stamp
1	76545	(electroplat\$10 or electrochem\$10 or electroly\$10 or electrodeposit\$10) near30 (oxid\$5 or nitri\$8)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2004/05/24 09:25
2	16456	((electroplat\$10 or electrochem\$10 or electroly\$10 or electrodeposit\$10) near30 (oxid\$5 or nitri\$8)) and (semiconductor or silicon)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2004/05/24 09:25
3	2137	((electroplat\$10 or electrochem\$10 or electroly\$10 or electrodeposit\$10) near30 (oxid\$5 or nitri\$8)) and (semiconductor or silicon)) and pad\$3	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2004/05/24 09:25
4	2451	"14" and (wir\$5 near5 (connect\$5 or bond\$5))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2004/05/24 09:30
5	655	((((electroplat\$10 or electrochem\$10 or electroly\$10 or electrodeposit\$10) near30 (oxid\$5 or nitri\$8)) and (semiconductor or silicon)) and pad\$3) and (wir\$5 near5 (connect\$5 or bond\$5))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2004/05/24 09:31
6	276	(((((electroplat\$10 or electrochem\$10 or electroly\$10 or electrodeposit\$10) near30 (oxid\$5 or nitri\$8)) and (semiconductor or silicon)) and pad\$3) and (wir\$5 near5 (connect\$5 or bond\$5))) and (wir\$5 near5 pad\$3)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2004/05/24 09:33

L Number	Hits	Search Text	DB	Time stamp
1	18473	wire near10 (oxid\$8 or nitri\$8)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/05/24 14:41
2	874	(wire near10 (oxid\$8 or nitri\$8)) and (wire near10 pad\$3)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/05/24 14:42
3	775	((wire near10 (oxid\$8 or nitri\$8)) and (wire near10 pad\$3)) and (semiconductor or silicon or wafer)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/05/24 14:42
4	7	((wire near10 (oxid\$8 or nitri\$8)) and (wire near10 pad\$3)) and (semiconductor or silicon or wafer)) and diaphragm	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/05/24 14:47
5	37346	wire near10 (nickel or ni or tantalum or ta or tungsten or w or molybdenum)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/05/24 14:48
6	1106	(wire near10 (nickel or ni or tantalum or ta or tungsten or w or molybdenum)) and (wire near10 pad)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/05/24 14:48
7	15	((wire near10 (nickel or ni or tantalum or ta or tungsten or w or molybdenum)) and (wire near10 pad)) and diaphragm	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/05/24 14:49
8	13	((wire near10 (nickel or ni or tantalum or ta or tungsten or w or molybdenum)) and (wire near10 pad)) and diaphragm) not (((wire near10 (oxid\$8 or nitri\$8)) and (wire near10 pad\$3)) and (semiconductor or silicon or wafer)) and diaphragm)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/05/24 14:49